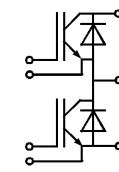




SEMITRANS 3

Absolute Maximum Ratings		$T_{case} = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_{case} = 25\text{ (80) °C}$	640 (450)	A
I_{CRM}	$T_{case} = 25\text{ (80) °C}$, $t_p = 1\text{ ms}$	1280 (900)	A
V_{GES}		± 20	V
T_{vj} , (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... +150 (125)	°C
V_{isol}	AC, 1 min.	4000	V
Inverse Diode			
$I_{FAV} = -I_C$	$T_{case} = 25\text{ (80) °C}$	390 (260)	A
I_{FRM}	$T_{case} = 25\text{ (80) °C}$, $t_p < 1\text{ ms}$	1280 (900)	A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_j = 150\text{ °C}$	2900	A
Freewheeling Diode			
$I_{FAV} = -I_C$	$T_{case} = 25\text{ (80) °C}$		A
I_{FRM}	$T_{case} = 25\text{ (80) °C}$, $t_p < 1\text{ ms}$		A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_j = 150\text{ °C}$		A

Characteristics		$T_{case} = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(TO)}$	$V_{GE} = V_{CE}$, $I_C = 16\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25\text{ (125) °C}$			2,6	mA
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1,0 (0,9)	1,15	V
r_{CE}	$V_{GE} = 15\text{ V}$, $T_j = 25\text{ (125) °C}$		1,75(2,75)	2,5	mΩ
$V_{CE(sat)}$	$I_C = 400\text{ A}$, $V_{GE} = 15\text{ V}$, chip level		1,7 (2,0)	2,15	V
C_{ies}			29		nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$		2,5		nF
C_{res}			2,5		nF
L_{CE}				20	nH
R_{CC+EE}	resistance, terminal-chip 25 (125) °C		0,35(0,5)		mΩ
$t_{d(on)}$	under following conditions: $V_{CC} = 600\text{ V}$, $I_C = 400\text{ A}$,		200		ns
t_r	$R_{Gon} = R_{Goff} = 4\text{ Ω}$, $T_j = 125\text{ °C}$,		60		ns
$t_{d(off)}$	$V_{GE} \pm 15\text{ V}$		770		ns
t_f			110		ns
$E_{on} (E_{off})$			42 (58)		mJ
Inverse Diode under following conditions:					
$V_F = V_{EC}$	$I_F = 300\text{ A}$; $V_{GE} = 0\text{ V}$; $T_j = 25\text{ (125) °C}$		2,0 (1,8)	2,5	V
$V_{T(TO)}$	$T_j = 25\text{ (125) °C}$		1,1	1,2	V
r_T	$T_j = 25\text{ (125) °C}$		2,3	3,3	mΩ
I_{RRM}	$I_F = 400\text{ A}$; $T_j = 125\text{ °C}$		140		A
Q_{rr}	$di/dt = 3000\text{ A/μs}$		45		μC
E_{rr}	$V_{GE} = 0\text{ V}$		10		mJ
FWD under following conditions:					
$V_F = V_{EC}$	$I_F = A$; $V_{GE} = 0\text{ V}$; $T_j = 25\text{ (125) °C}$				V
V_{TO}	$T_j = 25\text{ (125) °C}$				V
r_T	$T_j = 25\text{ (125) °C}$				mΩ
I_{RRM}	$I_F = A$; $T_j = 125\text{ °C}$				A
Q_{rr}	$V_{GE} = 0\text{ V}$				μC
E_{rr}					mJ
Thermal Characteristics					
$R_{th(j-c)}$	per IGBT			0,055	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,125	K/W
$R_{th(j-c)FD}$	per FWD				K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical Data					
M_s	to heatsink (M6)	3		5	Nm
M_t	for terminals (M5)	2,5		5	Nm
w				325	g



GB

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications

- AC inverter drives
- UPS
- Electronic welders

$I_{DC} \leq 500\text{ A}$ for $T_{Terminal} = 100\text{ °C}$

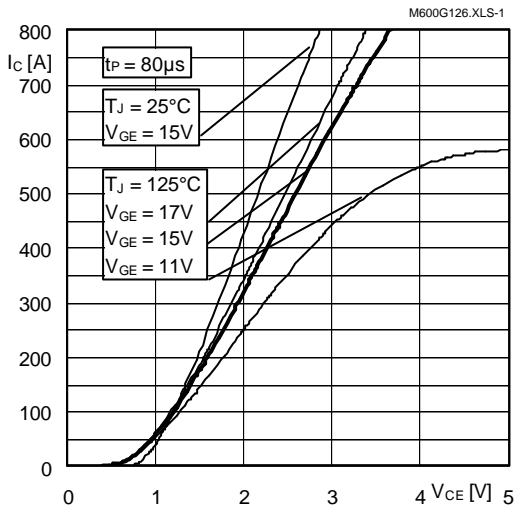


Fig. 1 Typ. output characteristic, inclusive $R_{CC} + E_{E'}$

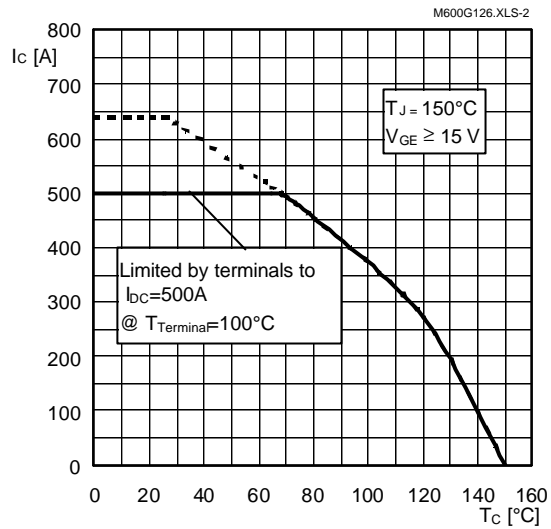


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

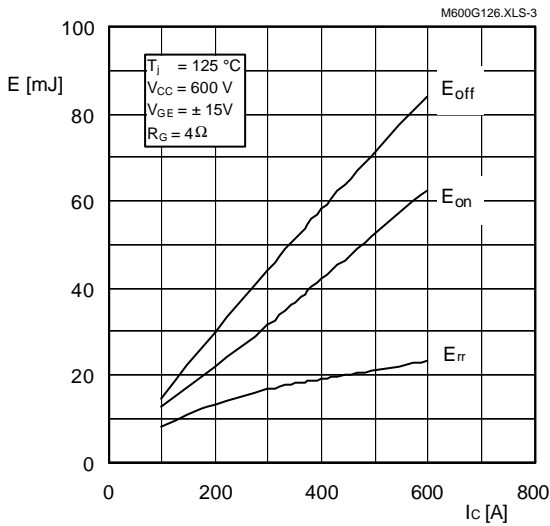


Fig. 3 Typ. turn-on /-off energy = $f(I_C)$

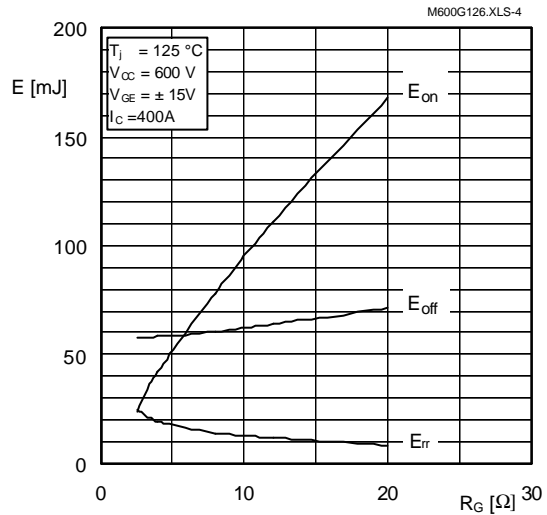


Fig. 4 Typ. turn-on /-off energy = $f(R_G)$

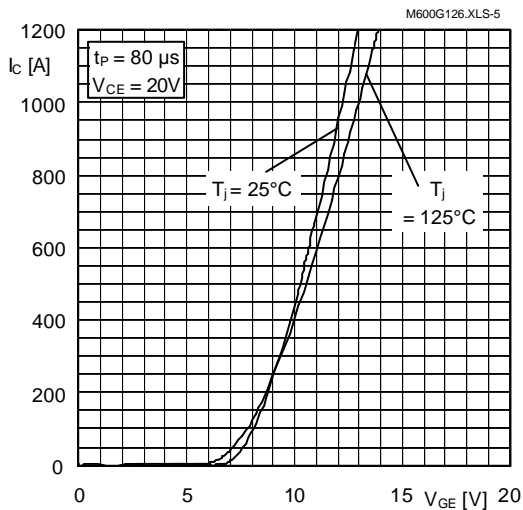


Fig. 5 Typ. transfer characteristic

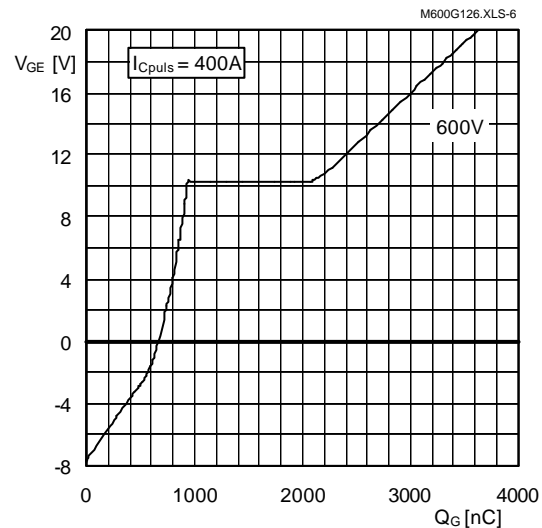


Fig. 6 Typ. gate charge characteristic

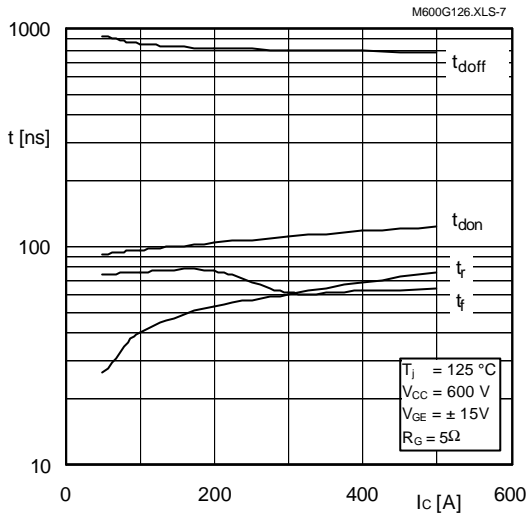


Fig. 7 Typ. switching times vs. I_c

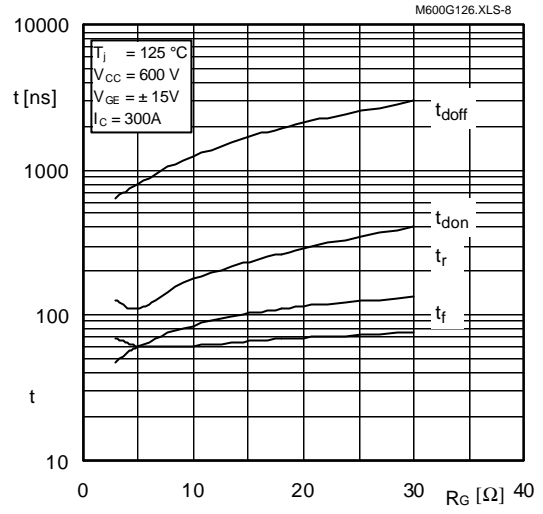


Fig. 8 Typ. switching times vs. gate resistor R_G

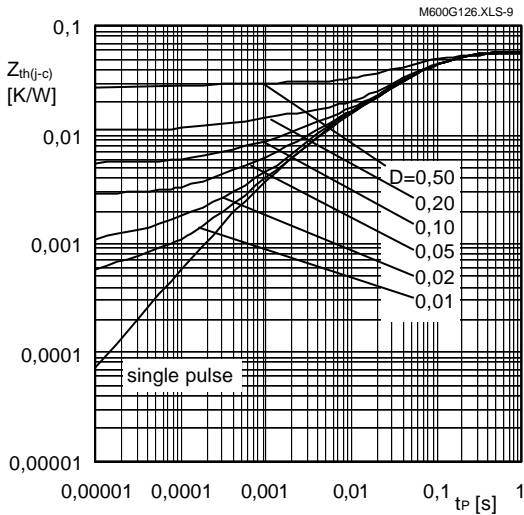


Fig. 9 Transient thermal impedance of IGBT $Z_{th(j-c)} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

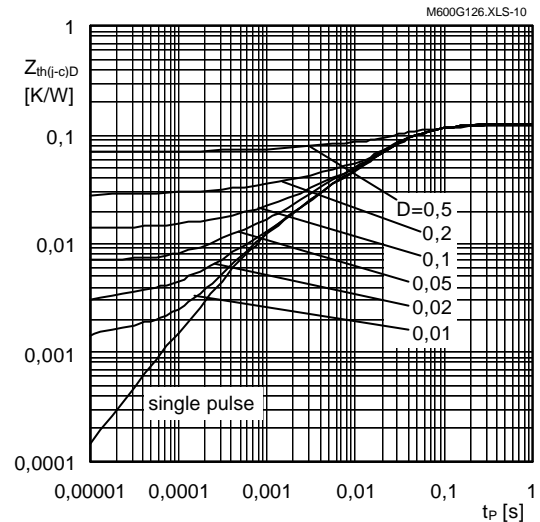


Fig. 10 Transient thermal impedance of FWD $Z_{th(j-c)D} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

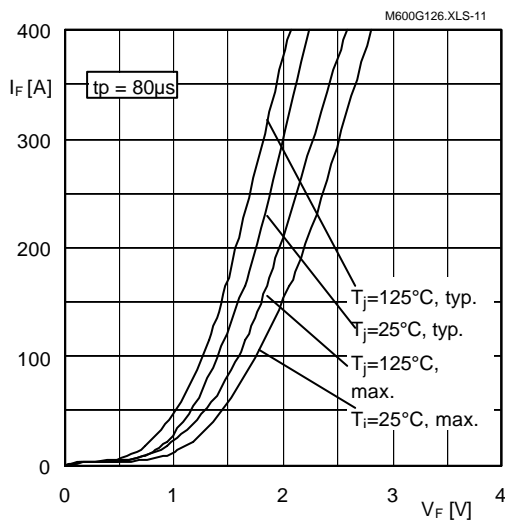


Fig. 11 CAL diode forward characteristic

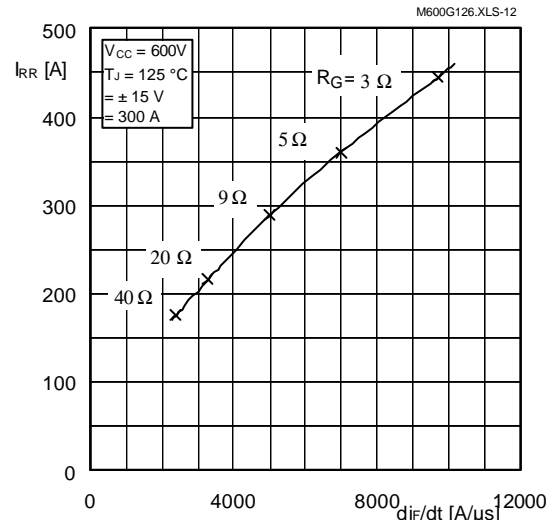
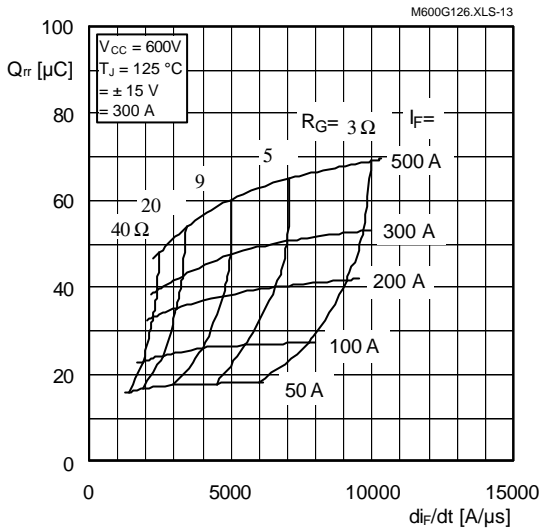


Fig. 12 Typ. CAL diode peak reverse recovery current

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This is an electrostatic discharge sensitive device (ESDS).

Please observe the international standard IEC 60747-1, Chapter IX.

Packing Unit	12 pcs	SEMIBOX D
Mounting Kit	10 pcs	Ident-No. 33321100

Fig. 13 Typ. CAL diode recovered charge

SEMISTRANS 3
Case D 56
UL Recognized
File no. E 63 532

SKM 600 GB 126 D

CASED56

Dimensions in mm

Case outline and circuit diagrams

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.